



#### 30V N-Channel Enhancement Mode MOSFET

Voltage

30 V

Current

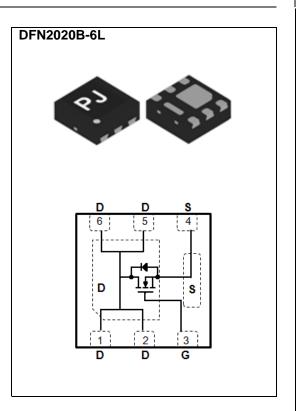
10 A

#### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@10A<11.5m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_D@6A<15m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std.. (Halogen Free)

#### **Mechanical Data**

- Case: DFN2020B-6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0003 ounces, 0.0086 grams



# **Maximum Ratings and Thermal Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage		V <sub>DS</sub>	30	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current	T <sub>A</sub> =25°C	I <sub>D</sub>	10		
Pulsed Drain Current		I <sub>DM</sub>	8	A	
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	2.0	W	
	Derate above 25°C		16	mW/°C	
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C	
Typical Thermal Resistance					
- Junction to Ambient (Note 4)		$R_{\theta JA}$	62.5	°C/W	





# Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}$ =0V, $I_D$ =250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1.0	1.7	2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =10A	-	7.5	11.5	mΩ
		V <sub>GS</sub> =4.5V,I <sub>D</sub> =6A	-	11	15	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 5)						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =15V, I <sub>D</sub> =10A, V <sub>GS</sub> =4.5V <sup>(Note 2,3)</sup>	-	6.9	-	nC
Gate-Source Charge	$Q_gs$		-	2.7	-	
Gate-Drain Charge	$Q_gd$		-	1.8	-	
Input Capacitance	Ciss		-	781	-	pF
Output Capacitance	Coss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	158	-	
Reverse Transfer Capacitance	Crss		-	92	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DS}$ =15V, $I_{D}$ =10A,	-	5.4	-	
Turn-On Rise Time	tr	$V_{GS}$ =10V, $R_{G}$ =6 $\Omega$ (Note 2,3)	-	86	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	20	-	
Turn-Off Fall Time	tf		-	10	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	_				- 1.5 A	_
Diode Forward Current	I <sub>S</sub>			_		^
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.73	1.0	V

#### NOTES:

- 1. Pulse width<a>300us</a>, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. R<sub>ΘJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 5. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

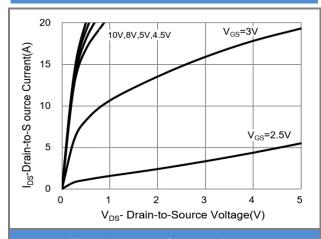
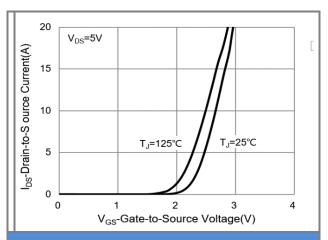


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

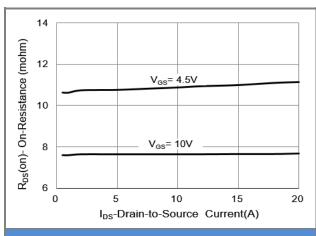


Fig.3 On-Resistance vs. Drain Current

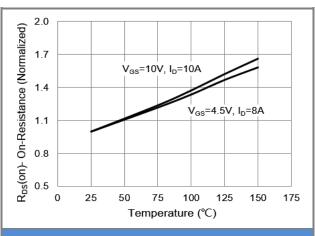
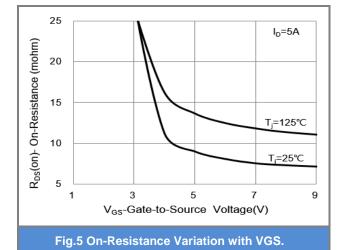


Fig.4 On-Resistance vs. Junction temperature



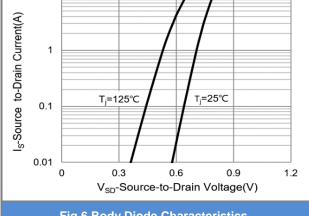


Fig.6 Body Diode Characteristics

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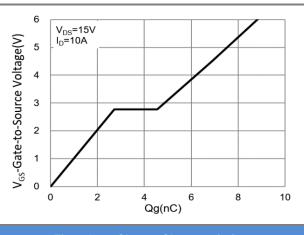


Fig.7 Gate-Charge Characteristics

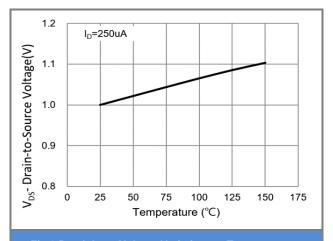


Fig.8 Breakdown Voltage Variation vs. Temperature.

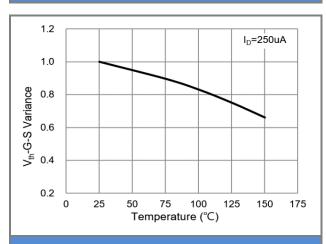


Fig.9 Threshold Voltage Variation with Temperature

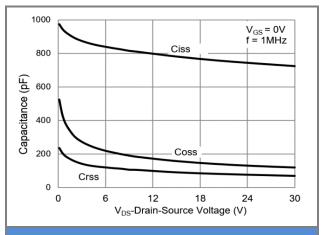


Fig.10 Capacitance vs. Drain-Source Voltage.

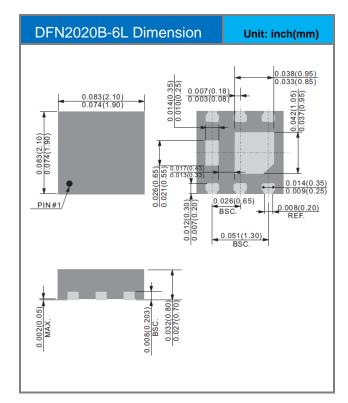


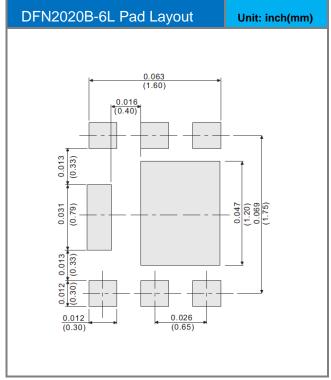


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ2408_R1_00001	DFN2020B-6L	3K pcs / 7" reel	408	Halogen free

### **Packaging Information & Mounting Pad Layout**









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